



WORLD INTELLECTUAL PROPERTY ORGANIZATION
International Bureau

PCT

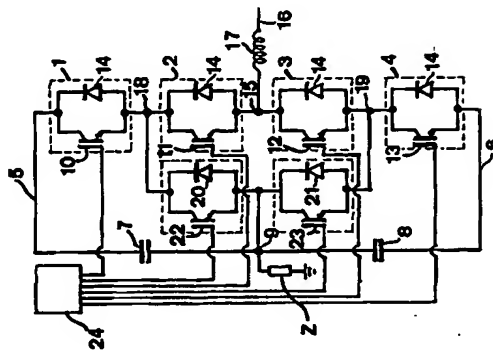
INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification:	H02M 7/197	(11) International Publication Number:	WO 99/40676
(21) International Application Number:	PCT/SE98/02273	(43) International Publication Date:	12 August 1999 (12.08.99)
(22) International Filing Date:	10 December 1998 (10.12.98)	(81) Designated States:	US, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).
(30) Priority Data:	980205-S 27 January 1998 (27.01.98) SE	Published	With international search report. In English translation (filed in Swedish).
(71) Applicant (for all designated States except US):	ASEA BROWN BOVERI AB [SE/SE]; S-721 28 Västerås (SE).		
(72) Inventor:	and		
(75) Inventor/Applicant (for US only):	BJELENGA, Bo [SE/SE]; Åkeravägen 7, S-730 50 Skutumpah (SE).		
(74) Agents:	BJERKÉN, Håkan et al.; Bjerkén Patentbyrå KB, P.O. Box 1274, S-801 37 Gävle (SE).		

(54) Title: A CONVERTER DEVICE

(57) Abstract

A device for converting alternating voltage into direct voltage and conversely comprises in a series connection between the poles (5, 6) of a direct voltage side at least four units (1-4) each consisting of a semiconductor element (10-13) of turn-off type and a first diode (14) connected in anti-parallel therewith. A first mid-point (15) of the series connection is connected to an alternating voltage phase line (16) and forms a phase output. Second mid-points (18, 19) of the series connection are connected to a mid-point of the direct voltage side (9) through such units (20, 22 and 21, 23, respectively). An apparatus (24) is adapted to control the semiconductor elements (11, 12) with a pulse width modulation frequency of at least one order of magnitude higher than the fundamental frequency of the alternating voltage of the phase line (16) and the rest of the semiconductor elements (10, 13, 22, 23) with a frequency being substantially lower and within or close to the frequency range one or a couple of times of said fundamental frequency.



FOR THE PURPOSES OF INFORMATION ONLY

Codes used to identify States party to the PCT on the front pages of pamphlets publishing international applications under the PCT.

AL	Albania	ES	Spain	SI	Slovenia
AM	Armenia	FI	Finland	SK	Slovakia
AT	Austria	FR	France	SN	Senegal
AU	Australia	GA	Gabon	SR	Sri Lanka
AZ	Azerbaijan	GB	United Kingdom	TD	Chad
BA	Bosnia and Herzegovina	GE	Georgia	TE	Togo
BB	Barbados	GH	Ghana	TG	Togo
BE	Belgium	GR	Greece	TM	Turkmenistan
BF	Burkina Faso	GU	Guinea	TR	Turkey
BG	Bulgaria	HU	Hungary	TT	Trinidad and Tobago
BJ	Benin	IE	Ireland	UA	Ukraine
BR	Brazil	IL	Israel	UG	Uganda
BY	Belarus	IS	Iceland	US	United States of America
CA	Canada	IT	Italy	UZ	Uzbekistan
CF	Central African Republic	JP	Japan	VN	Viet Nam
CG	Congo	KE	Kenya	ZW	Zimbabwe
CH	Switzerland	KG	Kyrgyzstan		
CI	Côte d'Ivoire	KP	Democratic People's Republic of Korea		
CM	Cameroon	NZ	New Zealand		
CN	China	PL	Poland		
CU	Cuba	PT	Portugal		
CZ	Czech Republic	RO	Romania		
DK	Denmark	RU	Russian Federation		
DE	Germany	SD	Sudan		
EE	Estonia	SE	Sweden		
EG	Egypt	SG	Singapore		
FR	France	LI	Liechtenstein		
GB	United Kingdom	LA	Laos		
GD	Grenada	LT	Lithuania		
GE	Georgia	LU	Luxembourg		
GF	French Guiana	LV	Latvia		
GG	Guernsey	MC	Monaco		
GH	Ghana	MD	Republic of Moldova		
GI	Gibraltar	MG	Madagascar		
GL	Greenland	MK	The former Yugoslav Republic of Macedonia		
GM	Gambia	ML	Mali		
GN	Guinea	MN	Mongolia		
GP	Guadeloupe	MR	Mauritania		
GQ	Equatorial Guinea	MW	Malawi		
GR	Greece	MX	Mexico		
GS	South Georgia and the South Sandwich Islands	NE	Niger		
GT	Guatemala	NL	Netherlands		
GU	Guam	NO	Norway		
GW	Guinea-Bissau	NP	Nepal		
GX	French Guiana	PZ	Panama		
GY	Guyana	PR	Puerto Rico		
HA	Haiti	RE	Reunion		
HE	Heard Island and McDonald Islands	RU	Russian Federation		
HN	Honduras	SD	Sudan		
HR	Croatia	SE	Sweden		
HT	Haiti	SG	Singapore		
HU	Hungary	SI	Slovenia		
IE	Ireland	SK	Slovakia		
IL	Israel	SN	Senegal		
IN	India	SR	Sri Lanka		
IO	British Indian Ocean Territory	TD	Chad		
IS	Iceland	TE	Togo		
IT	Italy	TG	Togo		
JE	Jersey	TJ	Tajikistan		
JM	Jamaica	TM	Turkmenistan		
JO	Jordan	TR	Turkey		
JP	Japan	TT	Trinidad and Tobago		
KE	Kenya	UA	Ukraine		
KG	Kyrgyzstan	UG	Uganda		
KH	Kampuchea	US	United States of America		
KI	Kiribati	UZ	Uzbekistan		
KM	Comoros	VN	Viet Nam		
KN	St Kitts and Nevis	ZW	Zimbabwe		
KO	South Korea				
KR	South Korea				
KU	Kuwait				
LA	Laos				
LB	Lebanon				
LC	St Lucia				
LE	Lebanon				
LI	Liechtenstein				
LK	Sri Lanka				
LR	Liberia				
LS	Lesotho				
LT	Lithuania				
LU	Luxembourg				
LV	Latvia				
LY	Libya				
MA	Morocco				
MC	Monaco				
MD	Republic of Moldova				
ME	Montenegro				
MG	Madagascar				
MH	Marshall Islands				
MI	Maldives				
ML	Mali				
MM	Myanmar				
MN	Mongolia				
MO	Macao				
MP	Mariana Islands				
MR	Mauritania				
MS	Montserrat				
MT	Malta				
MU	Mauritius				
MV	Maldives				
MW	Malawi				
MX	Mexico				
MY	Malaysia				
MZ	Mozambique				
NA	Namibia				
NC	New Caledonia				
NE	Niger				
NF	Norfolk Island				
NG	Nigeria				
NL	Netherlands				
NO	Norway				
NP	Nepal				
NR	Nauru				
NU	Niue				
NZ	New Zealand				
OM	Oman				
PA	Panama				
PE	Peru				
PF	French Polynesia				
PG	Papua New Guinea				
PH	Philippines				
PK	Pakistan				
PL	Poland				
PM	St Pierre and Miquelon				
PN	Pitcairn Islands				
PR	Puerto Rico				
PS	Palestine				
PT	Portugal				
PV	Puerto Rico				
PW	Palau				
PY	Paraguay				
QA	Qatar				
RE	Reunion				
RO	Romania				
RS	Serbia				
RU	Russian Federation				
RV	Viet Nam				
SA	Saudi Arabia				
SB	Solomon Islands				
SC	Seychelles				
SD	Sudan				
SE	Sweden				
SG	Singapore				
SH	St Helena				
SI	Slovenia				
SJ	Svalbard and Jan Mayen				
SK	Slovakia				
SL	Sierra Leone				
SM	San Marino				
SN	Senegal				
SO	Somalia				
SR	Sri Lanka				
SS	South Sudan				
ST	St Vincent and the Grenadines				
SV	El Salvador				
SW	Swaziland				
SY	Syria				
SZ	Swaziland				
TD	Chad				
TE	Togo				
TG	Togo				
TH	Thailand				
TJ	Tajikistan				
TK	Turkmenistan				
TL	Timor-Leste				
TM	Turkmenistan				
TN	Tunisia				
TO	Tonga				
TR	Turkey				
TT	Trinidad and Tobago				
TU	Turkmenistan				
TZ	Tanzania				
UA	Ukraine				
UG	Uganda				
US	United States of America				
UY	Uruguay				
UZ	Uzbekistan				
VA	Vatican City				
VC	St Vincent and the Grenadines				
VE	Venezuela				
VN	Viet Nam				
VU	Vanuatu				
WV	West Virginia				
WF	Wallis and Futuna				
WS	Samoa				
YE	Yemen				
YT	Mayotte				
ZA	South Africa				
ZD	Zambia				
ZM	Zambia				
ZW	Zimbabwe				

5

A converter device

FIELD OF THE INVENTION AND PRIOR ART

10

The present invention relates to a device for converting alternating voltage into direct voltage and conversely, which comprises a series connection of at least four units each consisting of a semiconductor element of turn-off type and a first diode connected in anti-parallel therewith, said series connection being arranged between two poles, a positive one and a negative one, of a direct voltage side of the device, an alternating voltage phase line connected to a first mid point, which is called phase output, of the series connection between two units while dividing the series connection into two parts, means adapted to provide a mid point between the two poles on said direct voltage side and put these poles on the same voltage but with opposite signs with respect to the mid point of the direct voltage side, a second mid point of each said part of the series connection being through a second diode with the conducting direction with respect to the phase output opposite to the conducting direction of the first diode in the unit arranged between this second mid point and the phase output connected to the mid point of the direct voltage side and an apparatus for controlling the semiconductor elements of the units to generate a train of pulses with determined amplitudes according to a pulse width modulation pattern on the phase output of the device by alternately connecting the alternating voltage phase line to at least the mid point, the plus pole and the minus pole of the direct voltage side.

35

Such devices may be used in all kinds of situations, in which direct voltage is to be converted into alternating voltage or conversely, in which examples of such uses are in stations of HVDC-plants (high voltage direct current), in which direct voltage normally is converted into a three-phase alternating voltage or conversely or in so called back-to-back-stations in which alternating voltage is firstly converted into direct voltage and this is then converted into alternating voltage, as well as in SVCs (Static Var Compensator), in which the direct voltage side consists of one or more capacitors hanging freely.

10

Such converter devices already known have a number of drawbacks, when these are used for transmitting high powers, and the present invention aims at a converter device being well suited to transmit high powers, although the invention is not restricted to this field of use, since a converter device of this type may very well find other field of uses. However, the case of transmitting high powers will for this reason hereinafter be discussed for eliminating but not in any way restricting the invention.

20

The device defined in the introduction is a so called multi-level converter, since it may deliver at least three different phase potentials on said phase output. Different types of such multi-level converters of this voltage stiff so called VSC-type (Voltage Source Converter) for high power applications have been described in the IEEE-article IEEE Trans. on Ind. Appl. Vol 32, no 3, 1996, pages 509-517. Three different types of multi-level converters are described therein, namely multi-level converters with clamping diodes, multi-level converters based upon flying capacitors and multi-level converters based upon cascaded converters. Only the two first ones are suitable for transmitting active power, such as for example in HVDC- and back-to-back-applications. The greatest problem of multi-level converters having clamping diodes is that the diode cost will be very high when the number of levels increases, so that for example in the case of

35

five levels the number of clamping diodes increases so that there is a need of more clamping diodes than said semiconductor elements of turn-off type. The converter devices with flying capacitors require for sure no clamping diodes, but they require instead a large number of capacitors, and the capacitor size increases with a comparatively large factor when the number of levels is increased, in which this factor is for example five to six when it is changed from three to five levels. Accordingly, this solution is also very costly.

10

SUMMARY OF THE INVENTION

The object of the present invention is to provide a converter device of the type defined in the Introduction, which is well suited for high voltage and high power applications and in which the drawbacks mentioned above of such devices already known are reduced to a large extent, primarily at an increased number of levels of the converter.

15

This object is according the invention obtained by connecting a semiconductor element of turn-off type in anti-parallel with each of said second diodes in a device of the type mentioned in the introduction, and that the apparatus is adapted to control the semiconductor elements of the units between the two second mid points to be turned on and turned off with a pulse width modulation frequency of at least one order of magnitude higher than the fundamental frequency of the alternating voltage of said alternating voltage phase line and to control the semiconductor elements connected in anti-parallel with said second diodes and in the units between the respective second mid point and the respective pole to be turned on and turned off with a frequency being substantially lower than said pulse width modulation frequency and within or close to the frequency range one or a couple of times said fundamental frequency.

30

35

By arranging a semiconductor element of turn-off type in this way in anti-parallel with said second diodes it is possible to also control the connection of the mid point of the direct voltage side to the second mid point, and it gets possible to obtain a desired pulse width modulation pattern at the connection of the phase line to the phase output by turning these semiconductor elements on and off as well as those arranged between said second mid point and the respective pole with a comparatively low frequency in the order of the fundamental frequency of the alternating voltage of the alternating voltage phase line, whereas the semiconductor elements of the "inner" units are turned on and off with a significantly higher frequency, more exactly the so called real pulse width modulation frequency. The frequency through which the semiconductor elements first mentioned are switched may for example be 50 or 60 Hz, while the pulse width modulation frequency is typically 1-2 kHz. This means that totally different, more exactly lower, demands are made upon the semiconductor elements first mentioned, which have not to be turned on and turned off with any high frequency, which means that for this semiconductor elements having a considerable better ability to hold high voltages may be used, since such high voltage semiconductor elements cannot take high frequencies without unacceptably high switching losses. Voltages in the order of 10-400 kV are normally handled in devices of this type, and this requires then a series connection of a higher number of semiconductor elements within each said unit for a series connection of a higher number of said units so as to distribute the voltage these have to hold in the blocking state among a high number of such semiconductor elements. Thus, in the present case it will be possible to use a lower number of semiconductor elements connected in series between said second mid point and the respective pole, since these may be of high voltage type, for example hold 4-6 kV instead of 2-3 kV, which means a considerable saving of costs and simplifies the control of the device. Semiconductor elements with a smaller component area may alternatively be used, which have a higher

5

10

15

20

25

30

35

thermal resistance, but which are available to a low cost, may be used for these semiconductor elements switched comparatively seldom. The same condition is valid for the semiconductor elements connected in anti-parallel with the second diodes and switched with a low switching frequency.

According to a preferred embodiment of the invention the apparatus is adapted to control the semiconductor elements connected in anti-parallel with said second diodes and in the units between the respective second mid point and the respective pole with a frequency coinciding with said fundamental frequency in absence of voltage harmonics in the alternating voltage phase line. A large difference in frequency between the control of these semiconductor elements and the other semiconductor elements is obtained by this and the advantages mentioned above of the invention with respect to the devices already known will by this be very remarkable. The apparatus is advantageously adapted, when said voltage harmonics occur to optionally carry out one or several additional switchings of the semiconductor elements connected in anti-parallel with said second diodes and those in the units between the respective second mid point and the respective pole within a fundamental frequency period, in which a switching is defined as comprising a turn-off and turn-on. It may in this way be compensated for such instabilities, in which the frequency in question may during a very short period of time become for example three times said fundamental frequency, but it is still considerably lower than the pulse width modulation frequency.

According to another preferred embodiment of the invention the apparatus is adapted to control the semiconductor elements of the units and the semiconductor elements connected in anti-parallel with said second diodes to alternately connect the alternating voltage phase line to an odd number of different levels, in which one of them is the mid point of the direct voltage side and just as many are positive as negative, in which said

number is n , which is at least five, that at least $(n-1)/2$ of said units are connected in series between the second and the first mid point, that it comprises $(n-3)/2$ so called flying capacitors and that each said flying capacitor is connected with one pole thereof to a mid point of said series connection, which is located between the phase output and the second mid point on the opposite side of the phase output with respect to the connection mid point belonging to the opposite pole thereof and has at least one unit between itself and the second mid point and another unit between itself and another capacitor connection or the phase output. Such a multi-level converter device with a higher number of levels than another converter device, which has for example three levels, results in a better adaptation of the pulse width modulation pattern to the sinus wave desired to be obtained downstream of an inductor or transformer arranged in said alternating voltage phase line, so that the harmonics generated during the conversion are reduced or the size of these inductors and/or filters for extinguishing such harmonics may be reduced, lower voltage differentials may be obtained for said inductors or transformers, so that stresses thereon may be reduced and these may be made less costly, and lower switching losses may be obtained. Such converter devices with a higher number of levels and the advantages associated therewith may according to this advantageous embodiment of the invention be obtained in a simple way and to a low cost. The advantages of the lower frequency of the semiconductor elements arranged between the respective second mid point and the respective pole as well as the semiconductor elements connected in anti-parallel with said second diodes have been discussed above. In addition thereto, this way to arrange a flying capacitor is very advantageous with respect to the arrangement of flying capacitors of the second type mentioned above of converter devices based upon flying capacitors, since a flying capacitor (s) are connected in such a way that they across the poles thereof will have a considerably lower voltage than in the case of the flying capacitors of the devices already known, more

5 exactly the voltage across the flying capacitor with the highest voltage thereacross is in the invention preferably not more than half the voltage across the entire series connection, which is of a great importance, since the power to be handled by a capacitor is proportional to the square of the voltage, so that the present invention enables a use of flying capacitors while avoiding the large number of clamping diodes which would be necessary in the case of a converter device of the type first mentioned, and the drawbacks of the second type of converter devices based upon flying capacitors has with respect to requirements of very large capacitors for a large number of levels of the converter device are nevertheless avoided. A large advantage of a converter device according to this embodiment of the invention is accordingly that it is possible to get a five-level-converter to a comparatively low additional cost with respect to a three-level-converter, and it will be easy to modify a three-level-converter.

20 According to a preferred embodiment of the invention n is 5 and said units are adapted to give the flying capacitor a voltage across the poles thereof substantially equal to $U/4$, in which U is the voltage between the two poles of the direct voltage side. The voltage of the flying capacitor may in this way be kept low and the size and the cost thereof may be kept at a low level.

25 According to another preferred embodiment of the invention the apparatus is adapted to control said units, when one pole of said flying capacitors is connected to said phase output so that the phase current passes said capacitor, to make this connection in one of two ways, which gives substantially the same phase potential on the phase outlet depending upon the instantaneous real level of the voltage between the poles of the capacitor, so that the capacitor is upon said connection charged for a voltage level thereof lower than desired and discharged for a voltage level thereof higher than desired. This process is possible thanks to the fact that there are two possible states giving al-

most the same potential on the phase output, in which one state may be used for charging the capacitor and the other for discharging the capacitor for a given direction of the phase current. This process means that the capacitance value of the capacitor may be kept at a minimum, with a time constant for the charging and the discharging, respectively, which is a suitable factor higher than the period of time during which the capacitor is normally switched in each of the positions for a given switching frequency.

10 Further advantages as well as advantageous features of the invention appear from the following description and the other dependent claims.

15 BRIEF DESCRIPTION OF THE DRAWINGS

With reference to the appended drawings, below follows a description of preferred embodiments of the invention cited as examples.

20 In the drawings:

Fig 1 is a circuit diagram illustrating a voltage stiff forced commutated three-level-converter already known connected to an alternating voltage network through inductors, in which only one phase leg is shown,

25 Fig 2 illustrates a converter device of three-level-type according to a first preferred embodiment of the invention, in which this is connected to a three-phase alternating voltage network through inductors,

30 Fig 3 illustrates the construction of the device according to Fig 2 for one phase of the alternating voltage network,

35

Fig 4 is a view corresponding to Fig 3 illustrating a five-level-converter device according to a second preferred embodiment of the invention, and

Fig 5 is a view corresponding to Fig 3 and 4, although somewhat simplified, of a seven-level-converter device according to a third preferred embodiment of the invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS OF THE INVENTION

The converter device shown in Fig 1 is a so called NPC (Neutral Point Clamped)-converter device with clamping diodes of a type well known, and this figure is shown here only for comparing the design of this converter device with a three-level-converter device according to a first preferred embodiment of the invention, which is shown in Fig 2 and 3 and now will be described with reference to these two figures. Only a part of the converter device connected to a phase of an alternating voltage phase line is shown in Fig 3, but it is also possible that this constitutes the entire converter device, when this is connected to a one-phase alternating voltage network. The converter device is a so called VSC-converter, which has four units 1-4, usually called transistor valves or alternatively thyristor valves, connected in series between the two poles 5, 6 of a direct voltage side of the device. Two capacitors 7, 8 connected in series are arranged between said two poles, and a point 9 (the mid point of the direct voltage side) therebetween is connected to ground through an impedance Z, in which this impedance may vary from 0 (= direct grounding of the mid point of the direct voltage side) to a value X (= impedance grounding of the mid point of the direct voltage side, through for example a resistance R or an inductance L) up to a value X_{max} (= ungrounded mid point, in which the grounding is only determined by the stray capacitance between the mid point of the direct voltage side and ground), so that the potentials $+U/2$ and $-U/2$, respectively, are in this way provided at the

respective pole, in which U is the voltage between the two poles 5, 6.

The units 1-4 are each made of a semiconductor element 10-13 of turn-off type, such as an IGBT or a GTO, and a first diode 14, a so called free-wheeling diode, connected in anti-parallel therewith. Although only one IGBT or GTO per unit has been shown this may stand for a plurality of IGBTs or GTOs connected in series and controlled simultaneously, which also normally is the case, since a comparatively high number of such semiconductor elements are required for holding the voltage to be held by each unit in the blocking state.

A first mid point 15 of the series connection between the two units 2 and 3, which constitutes the phase output of the converter, is connected to an alternating voltage phase line 16 through an inductor 17. Said series connection is in this way divided into two equal parts with two units 1, 2 and 3, 4, respectively, of each such part.

A second mid point 18, 19 of each said part of the series connection is through a second diode 20, 21 with a conduction direction with respect to the phase output opposite to the conducting direction of the first diode in the unit arranged between this second mid point and the phase output connected to the mid point 9 of the direct voltage side. A semiconductor element 22, 23 of turn-off type, such as an IGBT, is connected in anti-parallel with each second diode. It is also here valid that a great number of semiconductor elements may in practice be connected in series so as to distribute the voltage they have to hold in the blocking state among each of them, although one single semiconductor element has been shown in anti-parallel with each diode.

Furthermore, the device has an apparatus 24 adapted to control the different semiconductor elements and by that ensure that the

phase output 15 is connected to and receive the same potential as the pole 5, the pole 6 or the mid point 9 of the direct voltage side. This apparatus 24 and the arrangement thereof is here very simplified illustrated, and a separate such apparatus could in practice be arranged on high potential at each individual unit and these receive control signals from a control apparatus arranged on ground level. The function of the apparatus will be explained further below.

The converter device shown in Fig 3 differs with respect to the construction thereof from the NPC-converter device already known shown in Fig 1 by the replacement of the two clamping diodes 20', 21' by a unit consisting of a semiconductor element of turn-off type and a second diode connected in anti-parallel therewith.

By the new characteristic of the invention, i.e. to replace a clamping diode by a unit comprising a diode and a semiconductor element of turn-off type connected in anti-parallel therewith, completely new possibilities to obtain the different voltage levels desired to be obtained on the phase output 15 are obtained. More exactly it is possible to control the semiconductor elements 11, 12 of the units between the two second mid points 18, 19 through the apparatus 24 as before to be turned on and turned off with a pulse width modulation frequency, which preferably is in the order of 1-2 kHz and at least an order of magnitude, usually 20-40 times higher than the fundamental frequency of the alternating voltage of substantially sinusoidal design to be obtained on the alternating voltage phase line 16 on the opposite side of the inductor 17 with respect to the phase output 15. However, through said replacement of the clamping diodes the semiconductor elements 10, 13 of the units located between the respective pole and the respective second mid point have not to be turned on and turned off with a higher frequency than a frequency in the order of said fundamental frequency any longer, in which the frequency in

question preferably is identical to said fundamental frequency, but this may also be a multiple thereof, such as for example three times the fundamental frequency, especially when voltage harmonics occur on the alternating voltage phase line 16, in which the phase voltage may pass zero at more occasions than two times per period. The semiconductor elements 22 and 23 are also controlled with the same frequency as the semiconductor elements 10 and 13. The advantages of not being forced to control the semiconductor elements 10 and 13 with the same high frequency as the semiconductor elements 11 and 12 appear clearly from the disclosure above. +U/2 is obtained on the phase output 15 by turning the semiconductor elements 10 and 11 on, -U/2 is obtained by turning the semiconductor elements 12 and 13 on, while the mid point potential may be obtained either through turning the semiconductor elements 23 and 12 or the semiconductor elements 22 and 11 on.

It is illustrated in Fig 2 how a converter device according to Fig 3 is designed for converting direct voltage into alternating voltage and conversely between a direct voltage side and an alternating voltage network with three phases 25, 26, 27. A control for each phase is taking place in accordance with the description made with reference to Fig 3.

A converter device with respect to one phase according to a second preferred embodiment of the invention is illustrated in Fig 4 in a view corresponding to Fig 3, and this differs from the embodiment according to Fig 3 by the series connection of eight units 28-35 between the two poles 5 and 6, in which four are arranged on each side of the phase output 15. Furthermore, two units are arranged between the respective second mid point 18, 19 and the respective pole. Moreover, two units 36-39 are arranged instead of one such unit between each mid point 18 and 19, respectively, and the mid point 9 of the direct voltage side. Finally, a so called flying capacitor 40 is connected with one

heter, vilken är belägen mellan nämnda fasutgången 15 och den andra 18, 19 mittpunkten på motsatt sida om fasutgången mot anslutningsmittpunkten tillhörande dess motsatta pol och har en enhet mellan sig och den andra mittpunkten och en enhet mellan sig och fasutgången.

Hos denna anordning är det möjligt att uppnå fem olika nivåer på till den första mittpunkten 15 levererade pulser, nämligen $+U/2$, $+U/4$, 0 , $-U/4$ samt $-U/2$. Hos denna anordning är det meningen att de mellan de andra mittpunkterna 18 och 19 liggande enheterna styrs som ovan beskrivits med pulsbreddsmoduleringsfrekvens och enheterna 28, 29, 34, 35 liggande mellan respektive andra mittpunkt och pol samt enheterna 36, 37 och 38, 39 styrs med en betydligt lägre frekvens i storleksordningen av den grundfrekvens växelspänningen på växelspänningsfasledningen 16 har.

Därvid anger följande kopplingstillståndstabell de spänningsnivåer som kan uppnås på den första mittpunkten 15 och vilka kopplingstillstånd företrädesvis bör användas för att uppnå dessa spänningsnivåer.

	28 och 29	30	31	34 och 35	33	32	36 och 37	38 och 39
$V=U/2$	1	1	1	0	0	0	0	1
$V=U/4$	1	1	0	0	0	1	0	1
$V=U/4$	1	0	1	0	1	0	0	1
$V=0$	1	0	0	0	1	1	0	1
$V=0$	0	1	1	1	0	0	1	0
$V=-U/4$	0	1	0	1	0	1	1	0
$V=-U/4$	0	0	1	1	1	0	1	0
$V=-U/2$	0	0	0	1	1	1	1	0

25 Därvid står på konventionellt sätt 1 för tänd och 0 för släckt.

1 and 0 stand in a conventional way for turned on and turned off, respectively.

The following "rules" have been used in this table.

The following couples have the same state: 28, 29 and 38, 39, 34, 35 and 36, 37.

The following couples are complementary: 28, 29 and 36, 37, 34, 35 and 38, 39, 28, 29 and 34, 35, 30 and 33, 31 and 32, 36, 37 and 38, 39.

It appear from the table above that the intermediate voltage levels $+U/4$ and $-U/4$, respectively, which voltages may be obtained by switching in the flying capacitor 40, which is charged to the voltage $U/4$, in either direction. This may be obtained in two different ways, which charges or discharges the flying capacitor 40. Which one of these two ways is the one to be used is determined by the voltage of the flying capacitor 40, so that an apparatus corresponding to the apparatus 24 in Fig 3 controls the different semiconductor elements to choose the way resulting in a charging of the capacitor when the voltage across the poles thereof is too low and a discharging thereof when the voltage thereacross is too high with the aim to keep the voltage across the poles of the capacitor at $U/4$. The voltage across the capacitor is by that kept almost constant, which means a low energy content and the capacitor may by that be made small, i.e. with a low capacitance.

We assume for the sake of exemplifying that the frequency of the alternating voltage on the phase line 16 is for example 50 or 60 Hz and the converter only has to deliver active or reactive power at this fundamental frequency. The following is then valid:

we assume that the converter operates with a pulse width modulation frequency (PWM-frequency) of 1-2 kHz. The inner units 30-33 will then have a mean switching frequency of half the PWM-frequency, i.e. 0.5-1 kHz. The other units 28, 29, 34, 35, 36, 37 and 38, 39 will only switch with the fundamental frequency (50 or 60 Hz), and they will do so either at 0-current (28, 29 and 34, 35) or at 0-voltage (36, 37 and 38, 39). This means that the switching losses will be kept at a low level. This is valid especially for the semiconductor elements 28, 29, 34, 35, 36, 37, 38, 39. But also the semiconductor elements 30-33 will have a lower mean switching frequency than the corresponding 3-level-converter, so that high voltage semiconductor elements may be chosen, or alternatively semiconductor elements with a smaller area and a higher thermal resistance.

15 A seven-level-converter device constructed in the same way as the converter device according to Fig 4 is illustrated in Fig 5, and the function thereof appear from the description of the device according to Fig 4. Thus, two flying capacitors 43 are arranged for obtaining different voltage levels, in which the voltage across the outer capacitor 40 will be $U/3$ and across the inner capacitor 43 $U/6$. It is possible to continue in this way and by adding further flying capacitors obtain converter devices with more levels, i.e. 9, 11, ...

25 The valves are advantageously so designed that they give the flying capacitors a voltage U_x across the two poles thereof of $\frac{x \cdot U}{(n-1)}$, in which $x = 1, \dots, \frac{n-3}{2}$ and U is the voltage across the two poles of the direct voltage side. This means for example in the case of 9 levels $U_1 = U/8$, $U_2 = 2U/8$ and $U_3 = 3U/8$.

30 The invention is of course not in any way restricted to the preferred embodiments described above, but many possibilities to modifications thereof would be apparent to a man with ordinary skill in the art without departing from the basic idea of the invention.

The distribution of the units arranged on both sides of the different mid points of said series connection and between said second mid points and the respective pole may for example be different should that be desired, so that the voltage levels obtained on the first mid point 15 have another mutual relation than shown above.

CLAIMS:

1. A device for converting alternating voltage into direct voltage
and conversely, which comprises a series connection of at
least four units (1-4, 28-35) each consisting of a semi-
conductor element of turn-off type (10-13) and a first diode
(14) connected in anti-parallel therewith, said series
connection being arranged between two poles (5, 6), a
positive one and a negative one, of a direct voltage side of
the device, an alternating voltage phase line (16) connected
to a first mid point (15), which is called phase output, of the
series connection between two units while dividing the series
connection into two parts, means (9) adapted to provide a
mid point between the two poles on said direct voltage side
and put these poles on the same voltage but with opposite
signs with respect to the mid point of the direct voltage side,
a second mid point (18, 19) of each said part of the series
connection being through a second diode (20, 21) with the
conducting direction with respect to the phase output
opposite to the conducting direction of the first diode (14) in
the unit arranged between this second mid point and the
phase output connected to the mid point of the direct voltage
side and an apparatus (24) for controlling the semiconductor
elements of the units to generate a train of pulses with
determined amplitudes according to a pulse width modulation
pattern on the phase output (15) of the device by
alternatingly connecting the alternating voltage phase line to
at least the mid point, the plus pole and the minus pole of the
direct voltage side, characterized in that a semiconductor
element (22, 23) of turn-off type is connected in anti-parallel
with each of said second diodes, and that the apparatus is
adapted to control the semiconductor elements of the units
(2, 3, 30-33) between the two second mid points (18, 19) to
be turned on and turned off with a pulse width modulation
frequency of at least one order of magnitude higher than the
fundamental frequency of the alternating voltage of said

alternating voltage phase line and to control the
semiconductor elements (22, 23) connected in anti-parallel
with said second diodes (20, 21) and in the units (1, 4, 28,
29, 34, 35) between the respective second mid point and the
respective pole to be turned on and turned off with a
frequency being substantially lower than said pulse width
modulation frequency and within or close to the frequency
range one or a couple of times said fundamental frequency.

2. A device according to claim 1, characterized in that said ap-
paratus (24) is adapted to control the semiconductor ele-
ments (22, 23) connected in anti-parallel with said second
diodes (20, 21) and in the units (1, 4, 28, 29, 34, 35) be-
tween the respective second mid point and the respective
pole with a frequency being a multiple of said fundamental
frequency.

3. A device according to claim 1 or 2, characterized in that
said apparatus (24) is adapted to control the semiconductor
elements connected in anti-parallel with said second diodes
and in the units between the respective second mid point and
the respective pole with a frequency coinciding with said
fundamental frequency in absence of voltage harmonics in
the alternating voltage phase line.

4. A device according to claim 3, characterized in that said ap-
paratus (24) is adapted to optionally carry out one or several
additional switchings of the semiconductor elements
connected in anti-parallel with said second diodes and those
in the units between the respective second mid point and the
respective pole within a fundamental frequency period.

5. A device according to any of claims 1-4, characterized in
that it has four valves (1-4) with one or more said units con-
nected in series adapted to be controlled simultaneously
through the apparatus (24), each of said valves being de-

signed to take substantially the same portion of a voltage applied to one or more such valves connected in series as other such valves when the semiconductor elements included therein are turned off, that two valves (1, 2 and 3, 4), respectively are arranged between the phase output (15) and the respective pole (5, 6), that a valve (1,4) is arranged between the respective mid point (18, 19) and the respective pole, that a valve is arranged between the mid point (9) of the direct voltage side and said second mid point (18, 19), and that the apparatus (24) is adapted to carry out an alternating connection of three different potential levels to the phase output (15).

6. A device according to any of claims 1-4, characterized in that the apparatus (24) is adapted to control the semiconductor elements (10-13) of the units and the semiconductor elements (22, 23) connected in anti-parallel with said second diodes to alternately connect the alternating voltage phase line to an odd number of different levels, in which one of them is the mid point of the direct voltage side and just as many are positive as negative, in which said number is n, which is at least five, that at least (n-1)/2 of said units are connected in series between the second (18, 19) and the first mid point (15), that it comprises (n-3)/2 so called flying capacitors (40, 43), and that each said flying capacitor is connected with one pole thereof to a mid point (41, 42) of said series connection, which is located between the phase output and the second mid point on the opposite side of the phase output with respect to the connection mid point (41, 42) belonging to the opposite pole thereof and has at least one unit between itself and the second mid point and another unit between itself and another capacitor connection or the phase output.

7. A device according to claim 6, characterized in that n is 5, and that it has one said flying capacitor (40).

8. A device according to claim 7, characterized in that said units are adapted to give the flying capacitor (40) a voltage across the poles thereof substantially equal to U/4, in which U is the voltage between the two poles of the direct voltage side.

9. A device according to claim 7 or 8, characterized in that said series connection has eight valves (28-35), in which each valve is adapted to take substantially the same portion of a voltage applied to one or more such valves connected in series as other such valves when the semiconductor elements included therein are turned off, that four valves (28-35) are arranged between the phase output and the respective direct voltage pole, that two valves (28, 29, 34, 35) are arranged between the respective second mid point and the respective direct voltage pole, that a valve (31, 32) is arranged between the respective connection (41, 42) of the flying capacitor (40) to the series connection and the phase output (15), and that two valves (36-39) are connected in series between the mid point of the direct voltage side and said second mid point.

10. A device according to claim 6, characterized in that n is 7.

11. A device according to claim 9, characterized in that it has two flying capacitors (40, 43), and that the inner capacitor (43) connected by the poles thereof to said series connection closest to the phase output (15) is adapted to have a voltage of U/6 across the poles thereof and the second, outer capacitor (40) is adapted to have a voltage of U/3 across the poles thereof, in which U is the voltage between the two poles of the direct voltage side.

12.A device according to claim 6, characterized in that the valves are adapted to give the flying capacitors (40, 43) a voltage U_x across the two poles thereof of $\frac{x \cdot U}{(n-1)}$, in which $x = 1, \dots, \frac{n-3}{2}$ and U is the voltage across the two poles of the direct voltage side.

13.A device according to any of claims 6-12, characterized in that the apparatus (24) is adapted to control said unit, when one pole of said flying capacitors (40, 43) is connected to said phase output so that the phase current passes said capacitor, to make this connection in one of two ways, which gives substantially the same phase potential on the phase outlet depending upon the instantaneous real level of the voltage between the poles of the capacitor, so that the capacitor is upon said connection charged for a voltage level thereof lower than desired and discharged for a voltage level thereof higher than desired.

14.A device according to any of claims 1-13, characterized in that said semiconductor elements are IGBTs (Insulated Gate Bipolar Transistor).

15.A device according to any of claims 1-13, characterized in that said semiconductor elements are GTOs (Gate Turn-Off thyristor).

16.A device according to any of claims 1-15, characterized in that said direct voltage side is formed by a direct voltage network for transmitting high voltage direct current (HVDC) and the alternating voltage phase line belongs to an alternating voltage network.

17.A device according to any of claims 1-15, characterized in that it is a part of a SVC (Static Var Compensator) with the direct voltage side formed by capacitors hanging freely and

the alternating voltage phase line belonging to an alternating voltage network.

18. A device according to any of claims 1-17, characterized in that it has at least two alternating voltage phase lines (16, 25-27) included in a multiple-phase alternating voltage network, and that it comprises one said series connection and second diodes associated therewith and semiconductor elements of turn-off type connected in anti-parallel therewith for each phase line connected in parallel with each other between said poles of the direct voltage side.

19.A device according to claim 18, characterized in that the number of phases of the alternating voltage network is three.

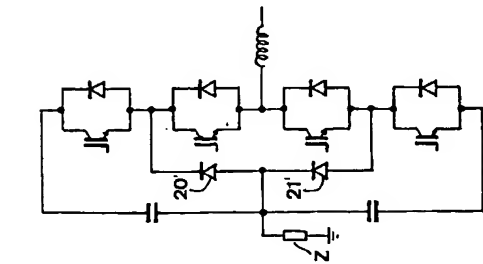


Fig 1

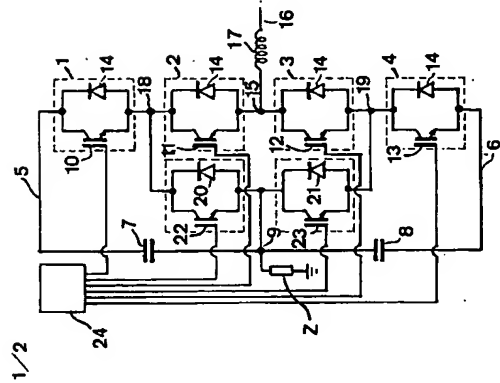


Fig 3

2/2

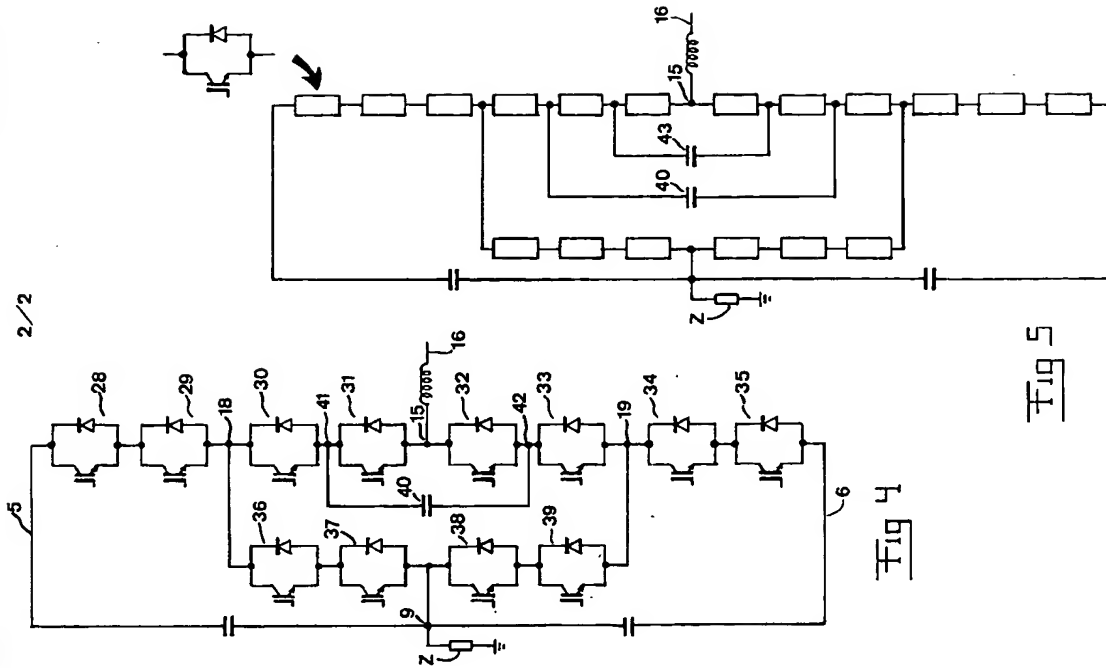


Fig 4

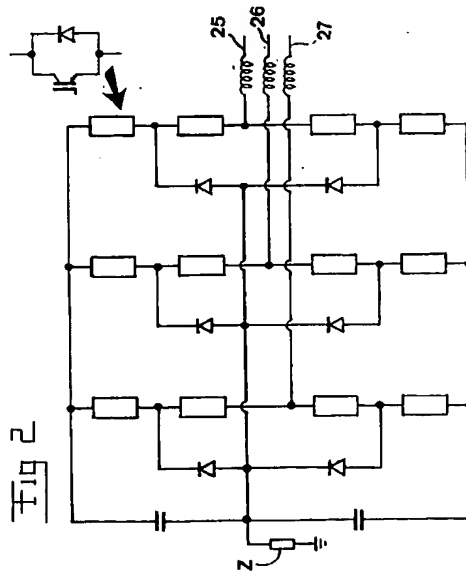


Fig 2

Fig 5

INTERNATIONAL SEARCH REPORT

INTERNATIONAL SEARCH REPORT Information on patent family members		International application No. PCT/SE 98/02273
A. CLASSIFICATION OF SUBJECT MATTER		
IPC6: H02M 7/797 According to International Patent Classification (IPC) or to both national classification and IPC:		
B. FIELDS SEARCHED		
Minimum documentation searched (classification system followed by classification symbols)		
IPC6: H02M, H03J, H03K		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched		
SE, DK, FI, NO classes as above		
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)		
MPI, PAJ		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 5617308 A (ANDREW P. WEISE ET AL), 1 Apr'11 1997 (01.04.97), column 3, line 34 - line 40, abstract	1-19
A	EP 0533158 A2 (HITACHI, LTD.), 24 March 1993 (24.03.93), figure 1, abstract	1-19
<input type="checkbox"/> Further documents are listed in the continuation of Box C. <input checked="" type="checkbox"/> See patent family annex.		
* Special categories of cited documents "A" document defining the general state of the art which is not considered to be of particular relevance "P" earlier document published on or after the international filing date "L" document which first threw doubt on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "G" document member of the same patent family		
Date of the actual completion of the international search		Date of mailing of the international search report
18 February 1999		22 March 1999 (22.03.99)
Name and mailing address of the ISA:		Authorized officer
Swedish Patent Office Box 5055, S-102 42 STOCKHOLM Facsimile No. + 46 8 666 02 86		Hans Bagge af Berga Telephone No. + 46 8 782 25 00